

Proposed

RF3800

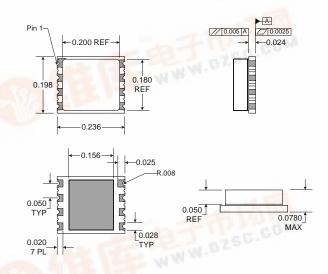
GaAs HBT PRE-DRIVER AMPLIFIER

Typical Applications

- Pre-Driver for 450MHz Basestation Amplifiers
- PA Stage for Commercial Wireless Infrastructure
- Class AB Operation for Cellular Radio and Wireless Local Loop

Product Description

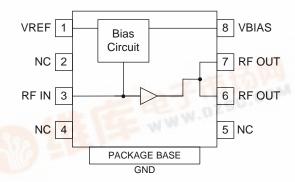
The RF3800 is specifically designed for wireless infrastructure applications in 450MHz. Using a highly reliable GaAs HBT fabrication process, this high-performance single-stage amplifier achieves high output power over a broad frequency range. The RF3800 also provides excellent efficiency and thermal stability through the use of a thermally-enhanced surface-mount AIN package. Ease of integration is accomplished through the incorporation of an optimized evaluation board design provided to achieve proper 50Ω operation. Various evaluation board bias configurations are available to address a broad range of wireless infrastructure applications.



Package Style: AIN

Optimum Technology Matching® Applied

☐ Si BJT ☐ GaAs HBT ☐ GaAs MESFET☐ Si Bi-CMOS ☐ SiGe HBT ☐ Si CMOS☐ InGaP/HBT ☐ GaN HEMT ☐ SiGe Bi-CMOS



Features

- 6W Output Power
- High Linearity
- 45% Power-Added Efficiency
- Thermally-Enhanced Packaging
- Broadband Platform Design Approach

Ordering Information

RF3800 GaAs HBT Pre-Driver Amplifier RF3800PCBA-416 Fully Assembled Evaluation Board

RF Micro Devices, Inc. 7628 Thorndike Road Greensboro, NC 27409, USA Tel (336) 664 1233 Fax (336) 664 0454 http://www.rfmd.com



Functional Block Diagram

Rev A1 040827

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